

1. Material Substrate GaAlAs (N Type) Removed
 Epitaxial Layer GaAlAs (P/N Type)

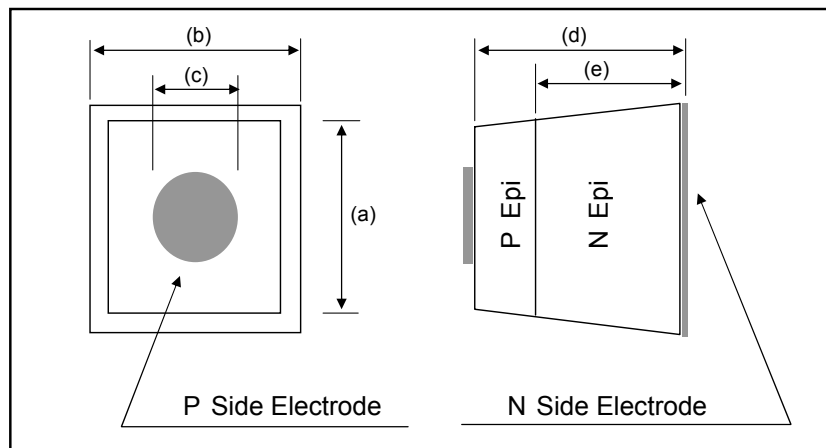
2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.7		V	IF=50mA
Reverse Voltage	V_R	4			V	IR=10uA
Power	P_O	13	18		mW	IF=50mA
Wavelength	λ_P		870		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	T_r		15		ns	
Fall Time	T_f		6.3		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data (a) Emission Area ----- 12.8mil x 12.8mil
 (b) Bottom Area ----- 13.8mil x 13.8mil
 (c) Bonding Pad ----- 150um
 (d) Chip Thickness ----- 7mil
 (e) Junction Height ----- 6.4mil



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